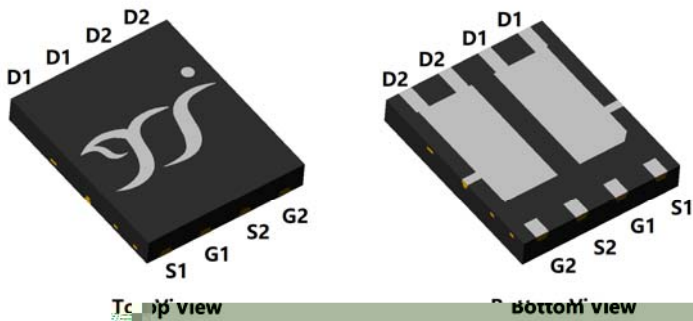


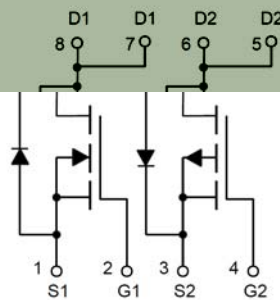
N-Channel and P-Channel Complementary MOSFET



Top view

Bottom view

DFN5060-8L



Product Summary

NMOS

• V_{DS}	100V
• I_D	25A
• $R_{DS(ON)}$ (at $V_{GS}=10V$)	26m Ω
• $R_{DS(ON)}$ (at $V_{GS}=6V$)	27m Ω
• $R_{DS(ON)}$ (at $V_{GS}=4.5V$)	30m Ω

PMOS

• V_{DS}	-100V
• I_D	-12A
• $R_{DS(ON)}$ (at $V_{GS}=-10V$)	120m Ω
• $R_{DS(ON)}$ (at $V_{GS}=-6V$)	125m Ω
• $R_{DS(ON)}$ (at $V_{GS}=-4.5V$)	130m Ω

General Description

- Split Gate Trench MOSFET technology
- Excellent package for heat dissipation
- Moisture Sensitivity Level 3
- Epoxy Meets UL 94 V-0 Flammability Rating
- Halogen Free

Applications

- Load switching
- Hard switched and high frequency circuits
- Uninterruptible power supply

■ Absolute Maximum Ratings ($T_A=25^\circ\text{C}$ unless otherwise noted)

Parameter		Symbol	NMOS	PMOS	Unit
Drain-source Voltage		V_{DS}	100	-100	V
Gate-source Voltage		V_{GS}	± 20	± 20	V
Drain Current	$T_A=25^\circ\text{C}$	I_D	5	2.5	A
	$T_A=100^\circ\text{C}$		3	1.6	
	$T_C=25^\circ\text{C}$		25	-12	
	$T_C=100^\circ\text{C}$		15	-7	
Pulsed Drain Current ^A		I_{DM}	80	-40	A
Avalanche energy ^B		EAS	64	72	mJ
Total Power Dissipation ^C	$T_A=25^\circ\text{C}$	P_D	2	1.5	W
	$T_A=100^\circ\text{C}$		0.8	0.6	
	$T_C=25^\circ\text{C}$		62	42	
	$T_C=100^\circ\text{C}$		25	16	
Junction and Storage Temperature Range		T_J, T_{STG}	-55 +150	-55 +150	$^\circ\text{C}$



YJG12NP10A

■ Thermal resistance

Parameter	Symbol	NMOS		PMOS		Units	
		Typ	Max	Typ	Max		
Thermal Resistance Junction-to-Ambient ^D	Steady-State	$R_{\theta JA}$	50	60	65	80	°C/W
Thermal Resistance Junction-to-Case	Steady-State	$R_{\theta JC}$	1.5	2	2.5	3	

■ Ordering Information (Example)

PREFERRED P/N	PACKING CODE	Marking	MINIMUM PACKAGE(pcs)	INNER BOX QUANTITY(pcs)	OUTER CARTON QUANTITY(pcs)	DELIVERY MODE
YJG12NP10A	F1	YJG12NP10A	5000	10000	100000	13" reel

■ NMOS Electrical Characteristics ($T_J=25$ unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
Static Parameter						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	100	-	-	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=100V, V_{GS}=0V$	-	-	1	μA
		$V_{DS}=100V, V_{GS}=0V, T_J=150^\circ C$	-	-	100	
Gate-Body Leakage Current	I_{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	± 100	nA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	1.2	1.7	2.5	V
Static Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS}=10V, I_D=25A$	-	19	26	m Ω
		$V_{GS}=6V, I_D=10A$	-	21	27	
		$V_{GS}=4.5V, I_D=5A$	-	22	30	
Diode Forward Voltage	V_{SD}	$I_S=25A, V_{GS}=0V$	-	0.9	1.3	V
Gate resistance	R_G	f=1MHz, Open drain	-	1.5	-	Ω
Maximum Body-Diode Continuous Current	I_S		-	-	25	A
Dynamic Parameters						
Input Capacitance	C_{iss}	$V_{DS}=50V, V_{GS}=0V, f=1MHz$	-	1200	-	pF
Output Capacitance	C_{oss}		-	400	-	
Reverse Transfer Capacitance	C_{rss}		-	10	-	
Switching Parameters						
Total Gate Charge	Q_g	$V_{GS}=10V, V_{DS}=50V, I_D=12.5A$	-	32	-	nC
Gate-Source Charge	Q_{gs}		-	11	-	
Gate-Drain Charge	Q_{gd}		-	5	-	
Reverse Recovery Charge	Q_{rr}	$I_F=12.5A, di/dt=100A/us$	-	85	-	nC
Reverse Recovery Time	t_{rr}		-	52	-	ns
Turn-on Delay Time	$t_{D(on)}$	$V_{GS}=10V, V_{DD}=50V, I_D=12.5A$ $R_{GEN}=2.2\Omega$	-	50	-	ns
Turn-on Rise Time	t_r		-	15	-	
Turn-off Delay Time	$t_{D(off)}$		-	70	-	
Turn-off fall Time	t_f		-	20	-	



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■ PMOS Electrical Characteristics (T_J=25°C unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
Static Parameter						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} = 0V, I _D =-250μA	-100	-	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =-100V, V _{GS} =0V	-	-	-1	μA
		V _{DS} =-100V, V _{GS} =0V, T _J =150°C	-	-	-100	
Gate-Body Leakage Current	I _{GSS}	V _{GS} = ±20V, V _{DS} =0V	-	-	±100	nA
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D =-250μA	-1.2	-1.7	-2.5	V
Static Drain-Source On-Resistance	R _{DS(on)}	V _{GS} =-10V, I _D =-12A	-	90	120	mΩ
		V _{GS} =-6V, I _D =-6A	-	93	125	
		V _{GS} =-4.5V, I _D =-3A	-	98	130	
Diode Forward Voltage	V _{SD}	I _S =-12A, V _{GS} =0V	-	-0.9	-1.2	V
Gate resistance	R _G	f=1MHz, Open drain	-	10	-	Ω
Maximum Body-Diode Continuous Current	I _S		-	-	-12	A
Dynamic Parameters						
Input Capacitance	C _{iss}	V _{DS} =-50V, V _{GS} =0V, f=1MHz	-	1100	-	pF
Output Capacitance	C _{oss}		-	110	-	
Reverse Transfer Capacitance	C _{rss}		-	10	-	
Switching Parameters						
Total Gate Charge	Q _g	V _{GS} =-10V, V _{DS} =-50V, I _D =-6A	-	20	-	nC
Gate-Source Charge	Q _{gs}		-	4	-	
Gate-Drain Charge	Q _{gd}		-	4.5	-	
Reverse Recovery Charge	Q _{rr}	I _F =-6A, di/dt=100A/us	-	140	-	nC
Reverse Recovery Time	t _{rr}		-	70	-	ns
Turn-on Delay Time	t _{D(on)}	V _{GS} =-10V, V _{DD} =-50V, I _D =-6A RGEN=2.2Ω	-	10	-	ns
Turn-on Rise Time	t _r		-	30	-	
Turn-off Delay Time	t _{D(off)}		-	77	-	
Turn-off fall Time	t _f		-	80	-	

A. Repetitive rating; pulse width limited by max. junction temperature.

B. NMOS: T_J=25°C, V_{DD}=50V, V_G=10V, R_G=25Ω, L=0.5mH, I_{AS}=16A.
PMOS: T_J=25°C, V_{DD}=-50V, V_G=-10V, R_G=25Ω, L=0.5mH, I_{AS}=-17A.

C. P_d is based on max. junction temperature, using junction-case thermal resistance.

D. The value of R_{θJA} is measured with the device mounted on 1 in² FR-4 board with 2oz. Copper, in the still air environment with T_A=25°C.
The maximum allowed junction temperature of 150°C. The value in any given application depends on the user's specific board design.



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NMOS Typical Electrical and Thermal Characteristics Diagrams

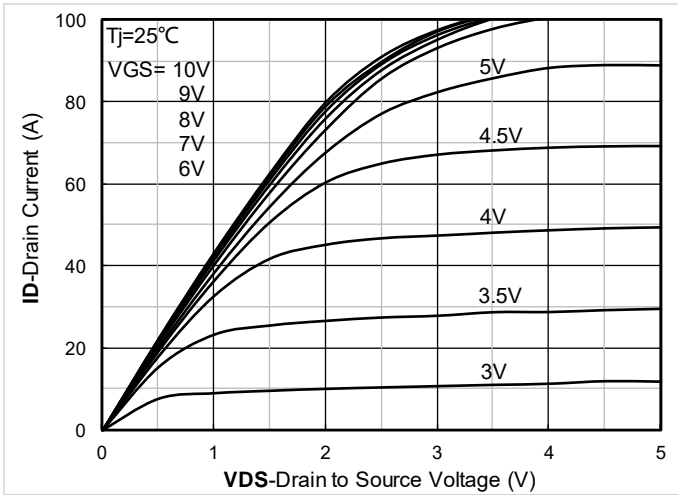


Figure 1. Output Characteristics

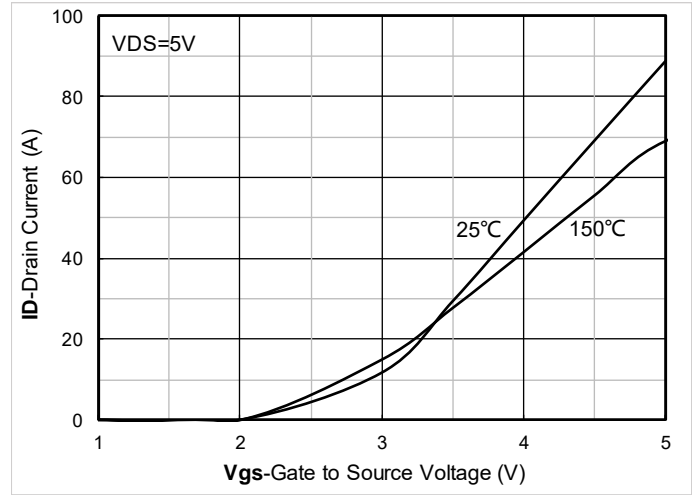


Figure 2. Transfer Characteristics

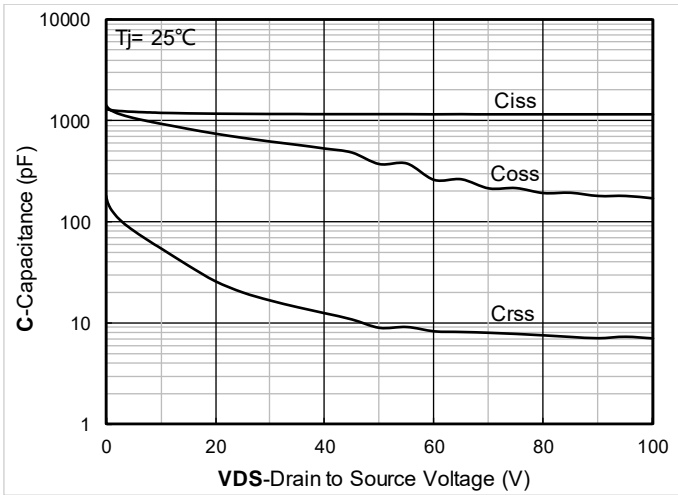


Figure 3. Capacitance Characteristics

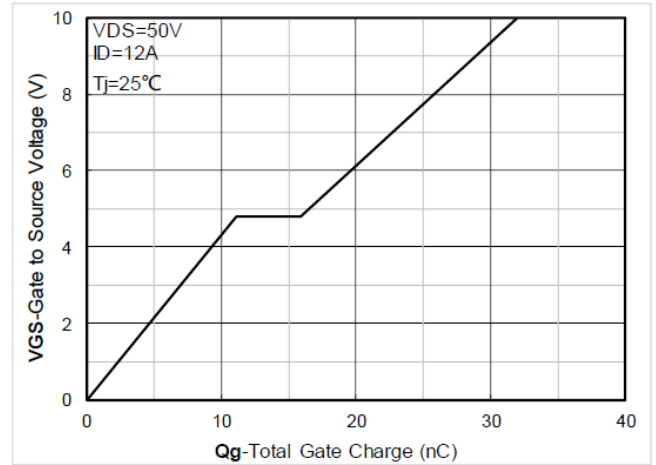


Figure 4. Gate Charge

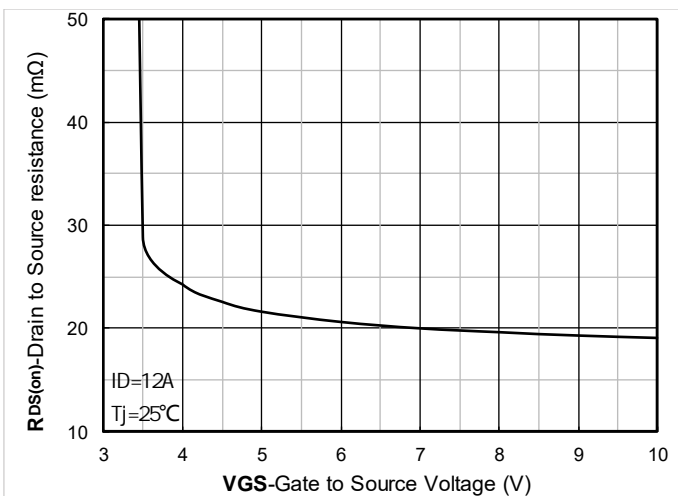


Figure 5. On-Resistance vs Gate to Source Voltage

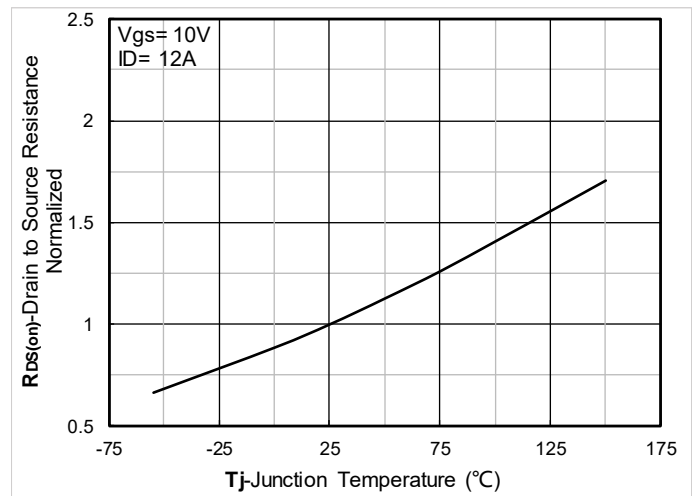


Figure 6. Normalized On-Resistance

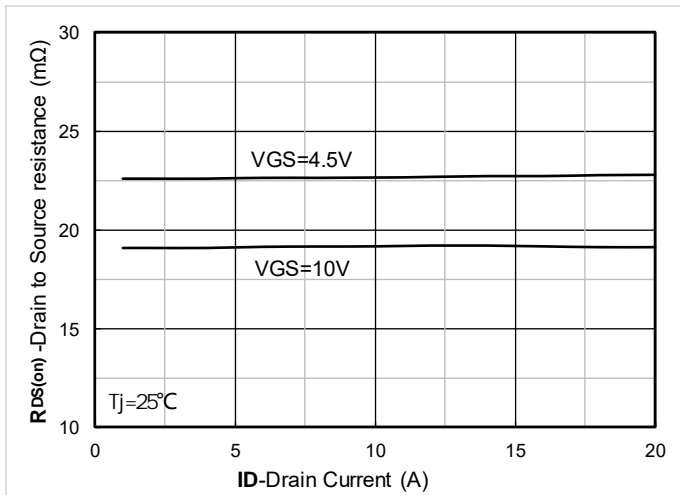
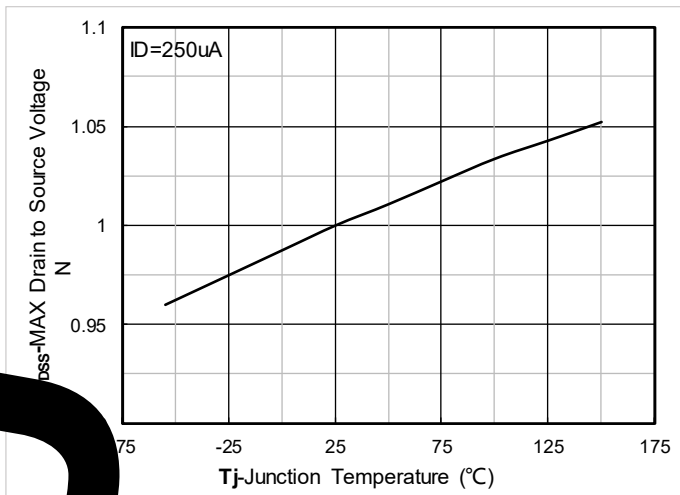


Figure 7. $R_{DS(on)}$ VS Drain Current

Figure 8. Forward characteristics of reverse diode





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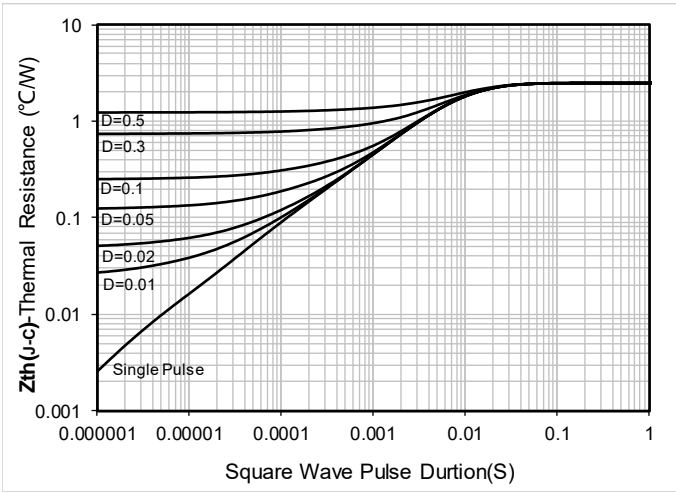


Figure 13. Maximum Transient Thermal Impedance

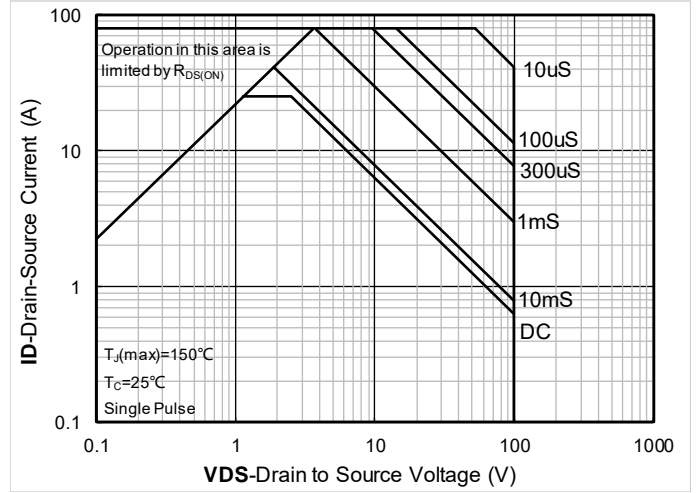
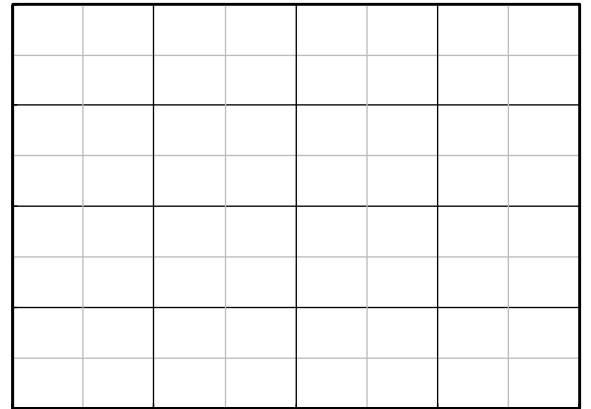
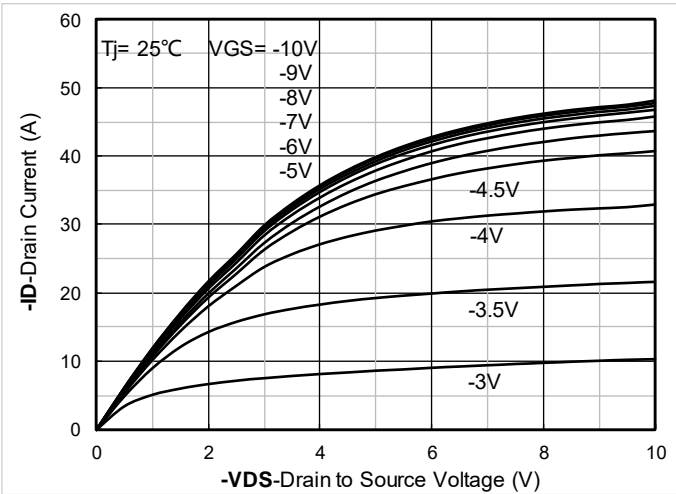


Figure 14. Safe Operation Area

PMOS Typical Electrical and Thermal Characteristics Diagrams





YJG12NP10A

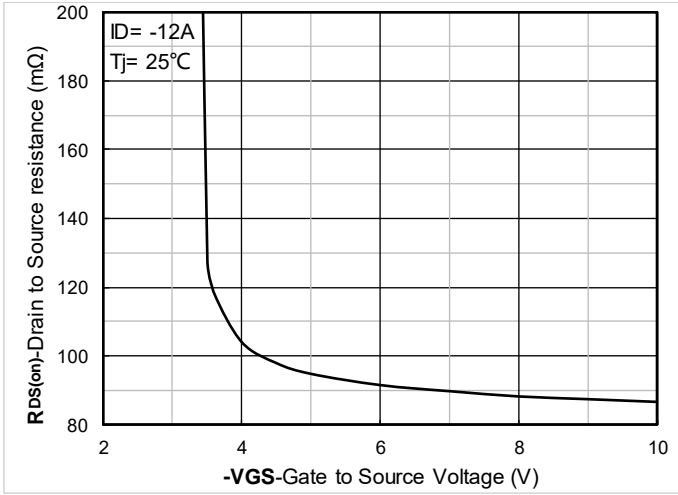


Figure 5. On-Resistance vs Gate to Source Voltage

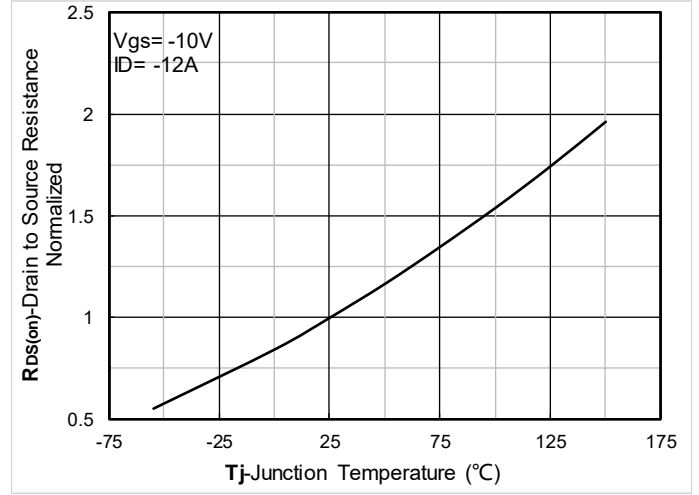


Figure 6. Normalized On-Resistance

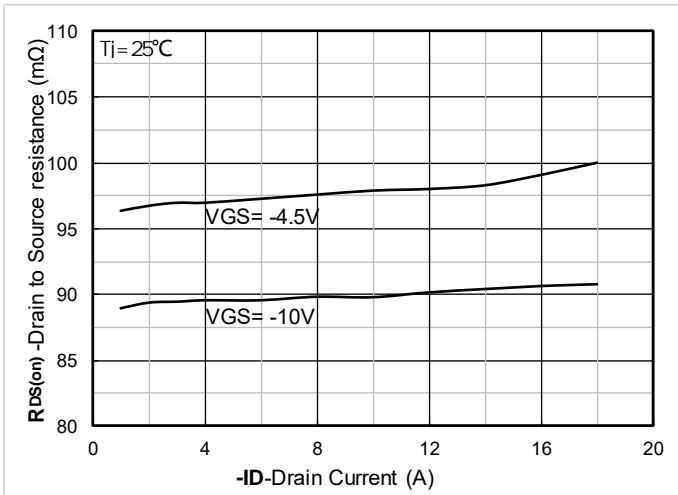


Figure 7. RDS(on) VS Drain Current

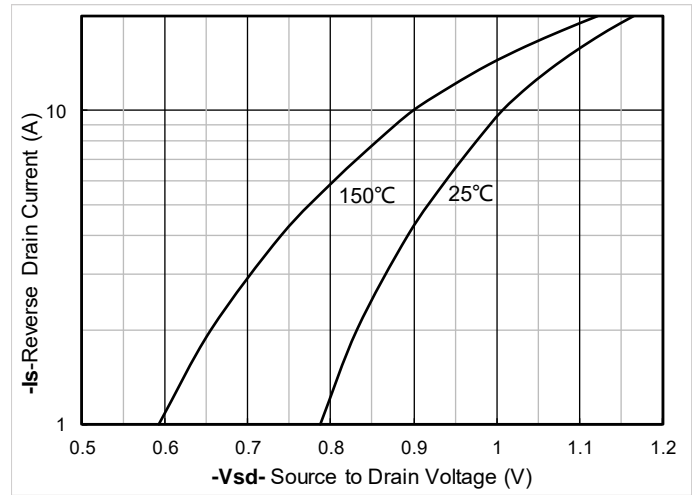


Figure 8. Forward characteristics of reverse diode

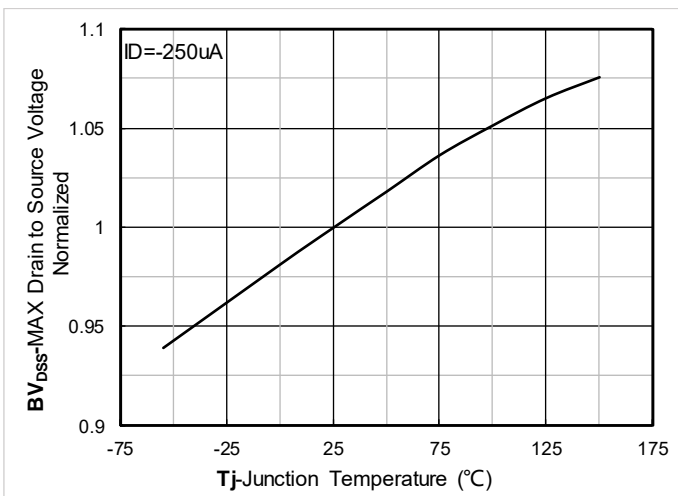


Figure 9. Normalized breakdown voltage

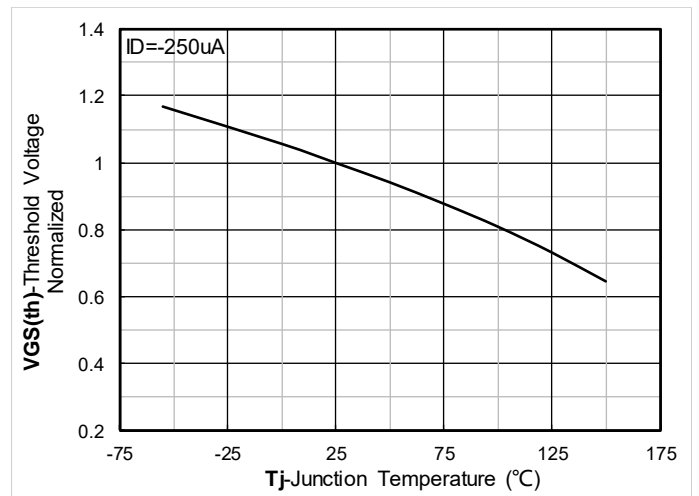


Figure 10. Normalized Threshold voltage



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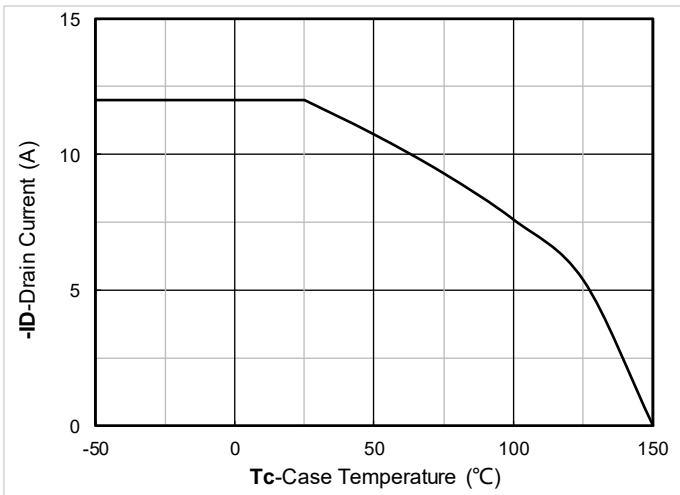


Figure 11. Current dissipation

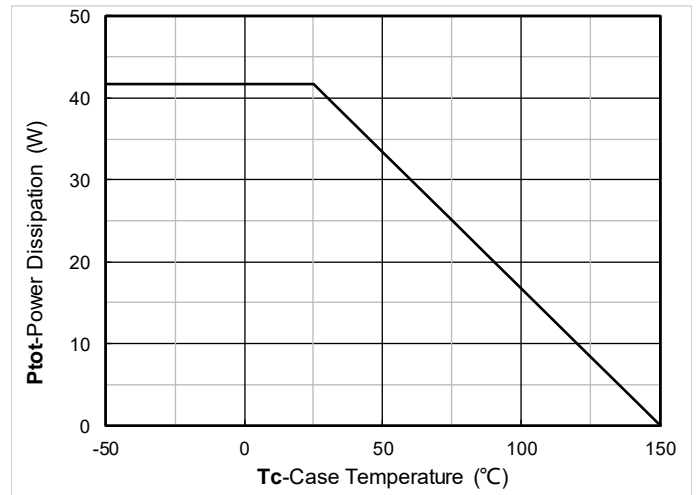


Figure 12. Power dissipation

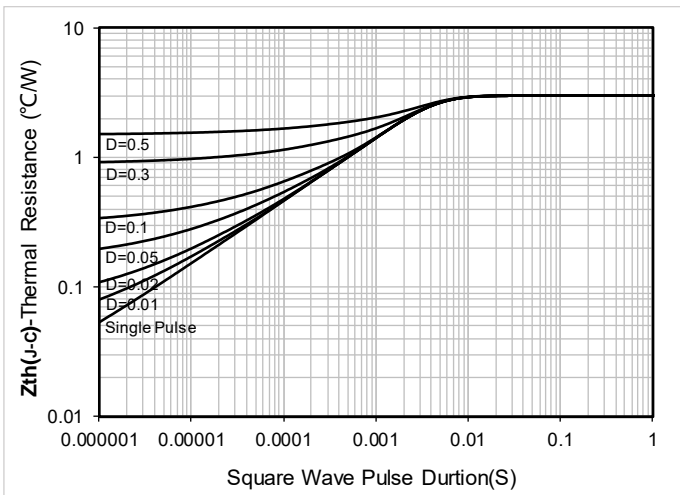


Figure 13. Maximum Transient Thermal Impedance

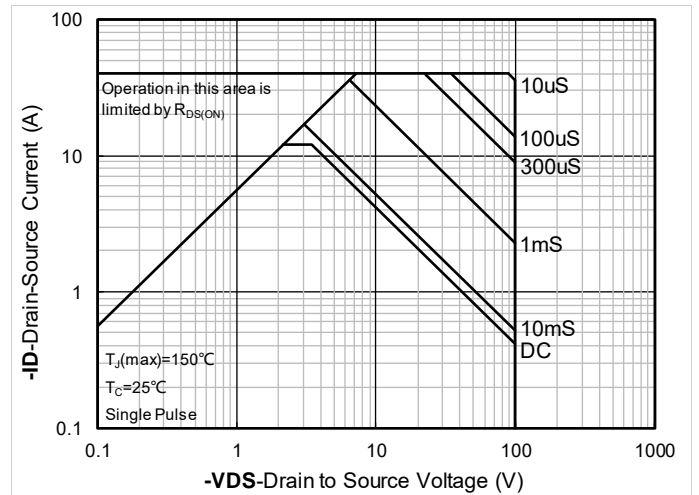
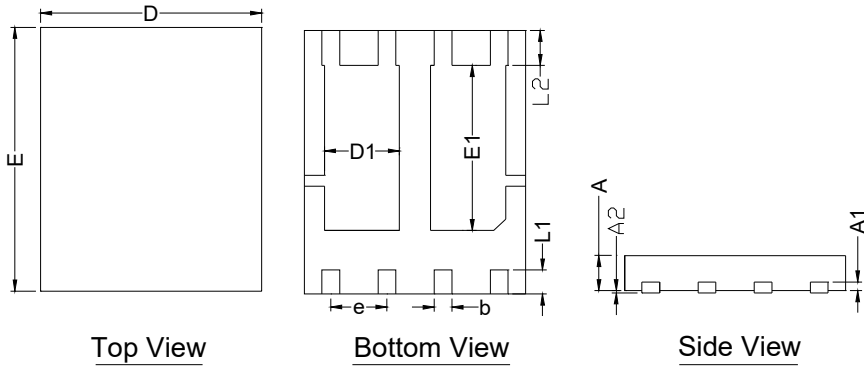


Figure 14. Safe Operation Area



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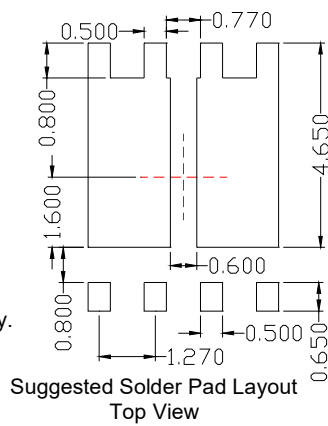
DFN5060-8L Package information



SYMBOL	MILLIMETER		
	MIN	NOM	MAX
D	4.90	5.00	5.10
E	5.90	6.00	6.10
A	0.70	0.80	0.90
A1	0.20 BSC		
A2			0.10
D1	1.60	1.70	1.80
E1	3.65	3.75	3.85
L1	0.45	0.55	0.65
L2	0.80 BSC		
b	0.30	0.40	0.50
e	1.27 BSC		

Note:

1. Controlling dimension: in millimeters.
2. General tolerance: ± 0.10 mm.
3. The pad layout is for reference purposes only.





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